

# Magnetisation and magnetic susceptibility of *Bi<sub>2</sub>Se<sub>3</sub>*

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# Magnetism of free electrons

Free electron trajectory is curved in magnetic field - orbital magnetism.

Spin magnetic moment is aligned along magnetic field - spin magnetism.

# Magnetism of electrons in solids.

- ▶ Bound electrons(localized)
- ▶ Band electrons(delocalized)
  - ▶ Diamagnetism Landau - orbital.
  - ▶ Pierls formula - orbital
  - ▶ Pauli paramagnetism - spin magnetism.

# McClure magnetism

Magnetic susceptibility of graphite is relatively big. For massive Dirac fermion.

$$\chi = -\frac{\mu_0 e^2 v^2}{6\hbar\pi} \frac{1}{m}$$

For massless Dirac fermion with non-zero temp.

$$\chi = -\frac{\mu_0 e^2 v^2}{24\hbar\pi} \frac{1}{T}$$

# Gauge invariant calculation results

Pierls substitution - derivation from 1-st principles.

$$M = \sum_n \int_{BZ} [n_F(E_{nk}) m_{nk} + e \frac{T}{\hbar} \log(1 + e^{-\frac{E-\mu}{T}}) \Omega_{nk}] \frac{d^2k}{4\pi^2}$$

$$\chi = -\frac{\mu_0 e^2}{12\hbar^2} \frac{Im}{\pi S} \int_{-\infty}^{+\infty} n_F(E) Tr[gh^{xx}gh^{yy} - gh^{xy}gh^{xy} - 4(h^x gh^x h^y gh^y - h^x gh^y h^x gh^y)] dE$$

Better than Landau diamagnetism.

# Model of 3D topological insulator

Surface states Hamiltonian

$$\begin{bmatrix} \mathbf{h}_1 & 0 \\ 0 & \mathbf{h}_2 \end{bmatrix}$$

$$h_1 = v_f k_y \sigma_x - v_f k_x \sigma_y + (m_0 + Bk^2) \sigma_z$$

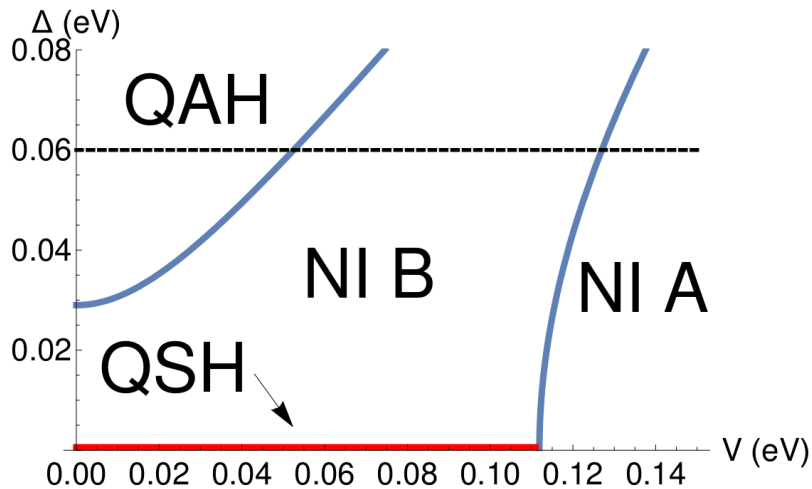
$$h_2 = v_f k_y \sigma_x + v_f k_x \sigma_y + (m_0 + Bk^2) \sigma_z$$

## Model of 3D topological insulator

$$H_{imp} = \begin{bmatrix} \Delta\sigma_z & 0 \\ 0 & -\Delta\sigma_z \end{bmatrix}$$

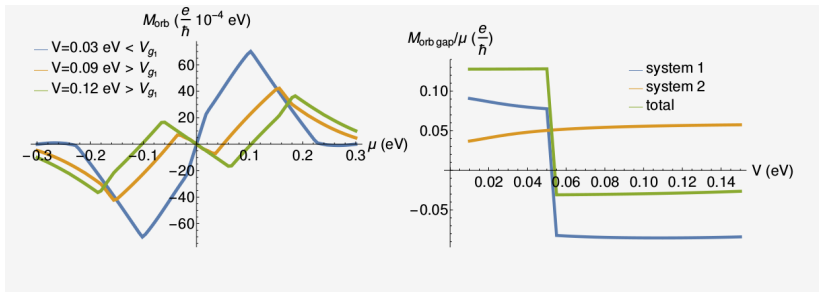
$$H_{el.field} = \begin{bmatrix} 0 & V\sigma_x \\ V\sigma_x & 0 \end{bmatrix}$$

## Phase structure





# Magnetization



## Magnetic susceptibility at $\mu = 0$

Gap closing between QAH and Insulator phase

$$\chi \propto -\frac{1}{\text{gap}}$$

$$\chi \propto -\frac{1}{T}$$

Gap closing between Insulator phases

$$\chi \propto +\frac{1}{\text{gap}^4}$$

$$\chi \propto +\frac{1}{T^4}$$

# Conclusion

- ▶ Magnetization in gap is linear in chemical potential with coefficient proportional to topological invariant.
- ▶ Susceptibility when gap is closing is diamagnetic as in McClure magnetism in one point of gap closing and paramagnetic with different power law behavior ( $+\frac{1}{T^4}$  instead of  $-\frac{1}{T^3}$ ) in other point.